

Features

- Ideally Suited for Automatic Insertion
- 150°C Junction Temperature
- Fast Switching speed
- Epitaxial Planar Die Construction

Mechanical Data

- Case: SOT-23, Molded Plastic
- Weight: 0.008 grams (approx.)
- Marking Code

Part Number	Marking	Continuous Reverse Voltage V_R (V)	Repetitive Peak Reverse Voltage V_{RRM} (V)
BAS19	JP	100	120
BAS20	JR	150	200
BAS21	JS	200	250

Maximum Ratings @ 25°C Unless Otherwise Specified

Parameter	Symbol	Value	Unit
Non-repetitive Peak Reverse Voltage @ t=1us	I_{FSM}	2.5	A
		0.5	
Average Rectified Forward Current	$I_{F(AV)}$	200 ⁽¹⁾	mA
Forward DC Current at $T_{amb}=25^\circ C$	I_F	200 ⁽²⁾	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Power Dissipation up to $T_{amb}=25^\circ C$	P_{tot}	250	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	430	°C/W
Operating & Storage Temperature	T_j, T_{STG}	-65~150	°C

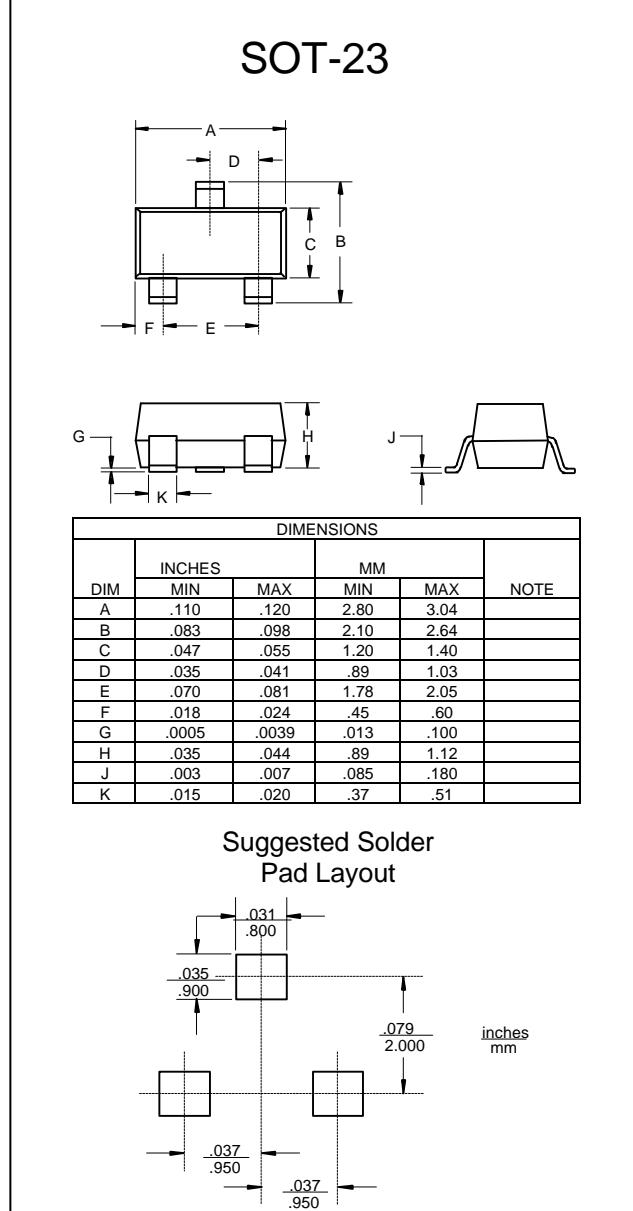
Notes: (1) Measured under pulse conditions;

Pulse time = $t_p \leq 0.3ms$

(2) Device on fiberglass substrate,

See layout on next page

**Small
Signal Diodes
250mW**



BAS19 thru BAS21

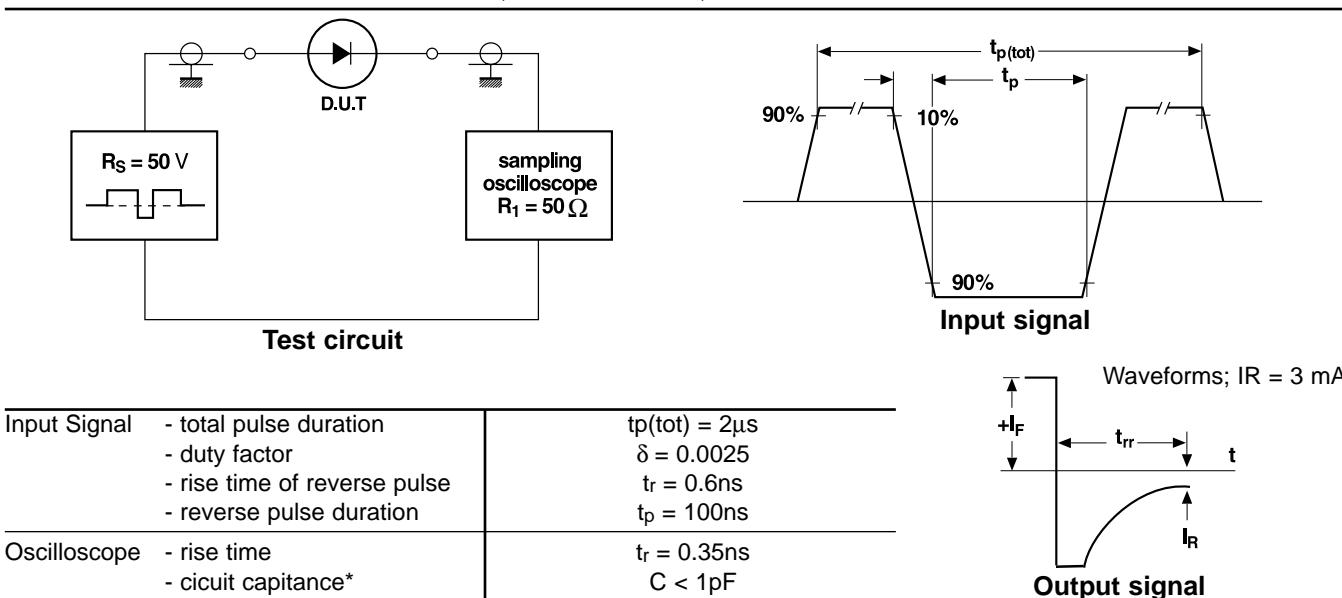
Electrical Characteristics

($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F = 100\text{mA}$ $I_F = 200\text{mA}$	—	—	1.0 1.25	V V
Leakage Current	I_R	$V_R = V_{R\max}$ $V_R = V_{R\max}; T_J = 150^\circ\text{C}$	—	—	100 100	nA μA
Dynamic Forward Resistance	r_f	$I_F = 10\text{mA}$	—	5	—	Ω
Capacitance	C_{tot}	$V_R = 0$ $f = 1\text{MHz}$	—	—	5	pF
Reverse Recovery Time (see figures)	t_{rr}	$I_F = 30\text{mA}, I_R = 30\text{mA}$ $I_{rr} = 3\text{mA}, R_L = 100\Omega$	—	—	50	ns

(1)Device on fiberglass substrate, see layout (SOT-23).

Test Circuit and Waveforms



*C = oscilloscope input capacitance + parasitic capacitance

Layout for $R_{\Theta JA}$ test

Thickness: Fiberglass 0.059 in. (1.5 mm)
Copper leads 0.012 in. (0.3 mm)

